

R-C Thermal Model Parameters

DESCRIPTION

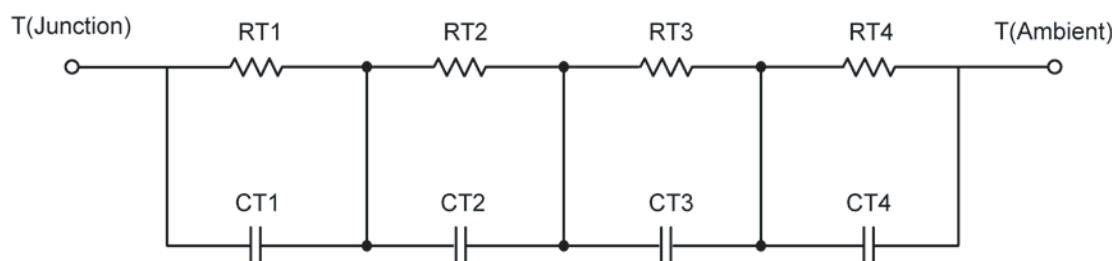
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

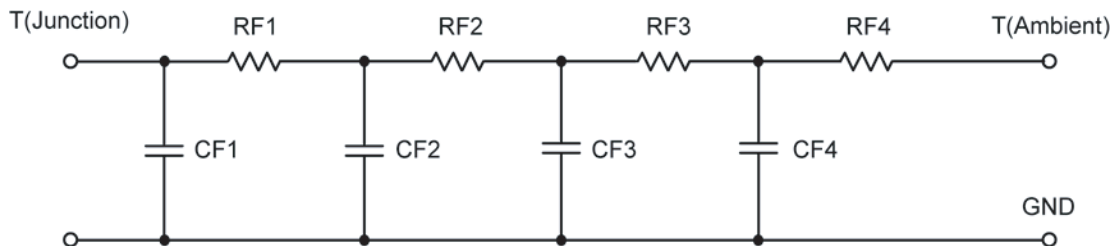
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION		
Thermal Resistance (°C/W)		
Junction to	Ambient	Case
RT1	23.2439	N/A
RT2	64.3366	N/A
RT3	66.7068	N/A
RT4	19.2650	N/A
Thermal Capacitance (Joules/°C)		
Junction to	Ambient	Case
CT1	971.1623 μ	N/A
CT2	1.3618	N/A
CT3	5.0988 m	N/A
CT4	204.4566 m	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)		
Junction to	Ambient	Case
RF1	28.3765	N/A
RF2	59.1441	N/A
RF3	23.5531	N/A
RF4	62.3025	N/A
Thermal Capacitance (Joules/°C)		
Junction to	Ambient	Case
CF1	756.1764 μ	N/A
CF2	3.6900 m	N/A
CF3	86.6763 m	N/A
CF4	1.2500	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

